

ABSTRACT OF THE DISCLOSURE

~~Art~~

A semiconductor device manufacturing method for forming on a semiconductor first and second oxide films and having different thicknesses comprises the steps of:

5 forming a silicon nitride film on a second oxide film formation area, and forming a first oxide film on a first oxide film formation area; and

removing the silicon nitride film and forming a second
10 oxide film on the second oxide film formation area.

SEARCHED - INDEXED - SERIALIZED - FILED